HALOGEN

FREE





2 Port, USB 2.0 High Speed (480 Mbps) Switch, DPDT Analog Switch

DESCRIPTION

The DG2720 is 2 Port high speed analog switch optimized for USB 2.0 signal switching. The DG2720 switch is configured in DPDT. It handles bidirectional signal flow, achieving a 620 MHz - 3 dB bandwidth with 5 pF load, and a port to port Crosstalk and isolation at - 49 dB.

Processed with high density sub micron CMOS, the DG2720 provide low parasitic capacitance. Signals are routed with minimized phase distortion and attain a bit to bit skew is as low as 40 pS.

The DG2720 is designed for a wide range of operating voltages, from 2.7 V to 4.3 V that can be driven directly from one cell Li-ion battery. On-chip circuitry protects against conditions when either the D+/D- lines are shorted to the V_{BUS} at the USB port. Additionally, logic control pins (S and $\overline{\text{OE}}$) can tolerate the presence of voltages that are above the supply power rail (V+). The control logic threshold is guaranteed to be (V_{IH} = 1.3 V/min).

Latch up current is greater than 300 mA, as per JESD78, and its ESD tolerance exceeds 8 kV.

Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL rating.

As a further sign of Vishay Siliconix's commitment, the DG2720 is fully RoHS complaint.

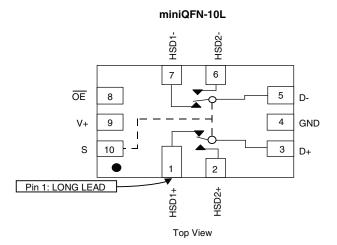
FEATURES

- Wide operation voltage range
- Low on-resistance, 5.7 Ω (typical at 3 V)
- Low capacitance, 5.6 pF (typical)
- 3 dB high bandwidth with 5 pF load: 620 MHz (typical)
- Low bit to bit skew: 40 pS (typical)
- · Low power consumption
- Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5 V when V+ = 0 V
- Logic (S and OE) above V+ tolerance
- Latch-up current greater than 300 mA per JESD78
- 8 kV ESD protection (HBM)
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: For definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- · Cellular phones
- · Portable media players
- PDA
- · Digital camera
- GPS
- · Notebook computer
- · TV, monitor, and set top box

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



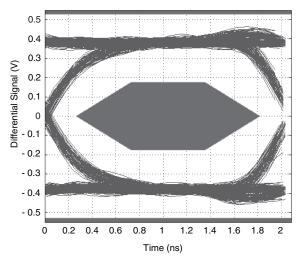
Document Number: 74593 S12-2498-Rev. D, 22-Oct-12 For technical questions, contact: analogswitchtechsupport@vishay.com



ORDERING INFORMATION					
Temp Range Package Part Number					
- 40 °C to 85 °C	miniQFN-10	DG2720DN-T1-E4			

TRUTH TABLE						
OE (Pin 8)	S (Pin 10)	Function				
0	0	D+ = HSD1+ and D- = HSD1-				
0	1	D+ = HSD2+ and D- = HSD2-				
1	Х	Disconnect				

PIN DESCRIPTIONS				
Pin Name Description				
ŌĒ	Bus Switch Enable			
S Select Input				
HSD1±, HSD2±, D±	Data Port			



High Speed Signal Quality Eye Diagram Test with V+ = 3.3 V

SUMMARY OF THE USB 2.0 SIGNAL QUALITY TEST RESULTS					
Compliance Test High Speed					
Signal Eye Test	Pass				
EOP Width	7.95 bits				
Measured Signal Rate	480.0009 MHz				
Consecutive Jitter Range	- 59.8 ps to 68.2 ps, RMS Jitter 26.8 ps				
Paired JK Jitter Range	- 49.7 ps to 51.4 ps, RMS Jitter 25.3 ps				
Paired KJ Jitter Range	- 61.3 ps to 58.5 ps, RMS Jitter 26.8 ps				





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter	Limit	Unit			
Reference to GND	V+	- 0.3 to 5	V		
neletefice to GIVD	S, OE, D±, HSD1±, HSD2±a	- 0.3 to (V+ + 0.3)	v		
Current (Any Terminal except S, OE, D±, H	30				
Continuous Current (S, OE, D±, HSD1±, HS	± 250	mA			
Peak Current (Pulsed at 1 ms, 10 % duty cy	± 500				
Storage Temperature (D Suffix)		- 65 to 150	°C		
Power Dissipation (Packages) ^b miniQFN-10 ^c		208	mW		
ESD (Human Body Model) I/O to GND		8	kV		
Latch-up (Current Injection)		350	mA		

Notes:

- a. Signals on S, $\overline{\text{OE}}$, D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.

SPECIFICATIONS V+ = 3 V									
Parameter	Symbol	Test Conditions	Temp.	Limits - 40 to 85 °C			Uni		
raiametei	Symbol	Otherwise Unless Specified		Min.	Тур.	Max.	t		
Analog Switch				L					
Analog Signal Range ^d	V _{ANALOG}	r _{DS(on)}	Full	0		V+	V		
On-Resistance	R _{DS(on)}	V+ = 3 V, I _{D±} = 8 mA, V _{HSD1/2±} = 0.4 V	Room		5.7	7			
On-Hesistance	DS(on)	V 1 = 0 V, 1 _{D±} = 0 111/V, V _{HSD1/2±} = 0:4 V	Full			9			
On-Resistance Match ^d	ΔR_{ON}	$V+ = 3 V$, $I_{D\pm} = 8 mA$, $V_{HSD1/2\pm} = 0.4 V$	Room		0.35		Ω		
On-Resistance Resistance Flatness ^d	R _{ON} Flatness	$V+ = 3 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0 \text{ V}, 1 \text{ V}$	Room		2				
Switch Off Leakage Current	I _(off)	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 3 \text{ V}, $ $V_{\text{D}\pm} = 3 \text{ V}, 0.3 \text{ V}$	Full	- 100		100	4		
Channel On Leakage Current	I _(on)	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 4 \text{ V}, $ $V_{\text{D}\pm} = 4 \text{ V}, 0.3 \text{ V}$	Full	- 200		200	nA		
Digital Control	Digital Control								
Input Voltage High	V _{INH}	V+ = 3 V to 3.6 V	Full	1.3					
input voltage riigii		V+ = 4.3 V	Full	1.7			V		
Input Voltage Low	V_{INL}	V+ = 3 V to 4.3 V	Full			0.5			
Input Capacitance	C _{IN}		Full		5.6		pF		
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$ or V+	Full	- 1		1	μΑ		



SPECIFICATIONS V+ = 3 V							
_		Test Conditions		Limits			
Parameter	Symbol	Otherwise Unless Specified	Temp. ^a	Min.b	10 to 85	Max.b	Unit
Dynamic Characteristics				WIIII.	Typ.	wax.	
Break-Before-Make Time ^{e, d}	t _{BBM}		Room		5		
		V+ = 3 V, $V_{D1/2 \pm}$ = 1.5 V, R_L = 50 Ω,	Full				
Enable Turn-On Time ^{e, d}	$t_{ON(EN)}$	$C_{L} = 35 \text{ pF}$	Full	'		30	ns
Enable Turn-Off Time ^{e, d}	t _{OFF(EN)}		Room			25	
			Full				
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 0 V$			0.5		рC
Off-Isolation ^d	OIRR	V+ = 3 V to 3.6 V, R_L = 50 Ω , C_L = 5 pF,			- 30		dB
Crosstalk ^d	X _{TALK}	f = 240 MHz			- 49		
Bandwidth ^d	BW	V+ = 3 V to 3.6 V, R_L = 50 Ω, C_L = 5 pF, - 3 dB			620		MHz
O 10%0 : d	C _{D1± (off)}		Room		4		pF
Channel-Off Capacitance ^d	C _{D2± (off)}	V 00V (4 MIL-			4		
0, 10,0 t, d	C _{D± (off)}	V+ = 3.3 V, f = 1 MHz			5.6		
Channel-On Capacitance ^d	C _{D± (on)}				11		
Channel-to-Channel Skew ^d	t _{SK(O)}		1		50		ps
Skew Off Opposite Transitions of the Same Output ^d	t _{SK(p)}	V+ = 3 V to 3.6 V, R_L = 50 Ω , C_L = 5 pF			20		
Total Jitter ^d	t _J				200		
Power Supply							ı
Power Supply Range	V+			2.6		4.3	V
Power Supply Current	l+	$V_{IN} = 0 \text{ V, or V+}$	Full			2	μΑ

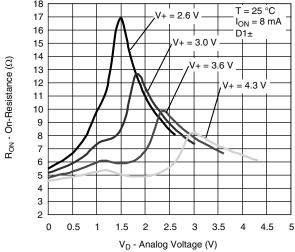
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Crosstalk measured between channels.

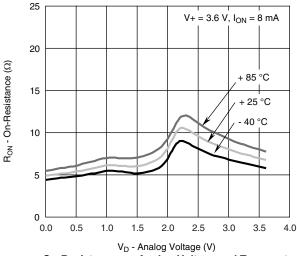
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



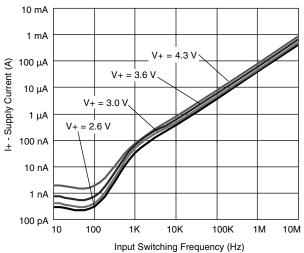
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



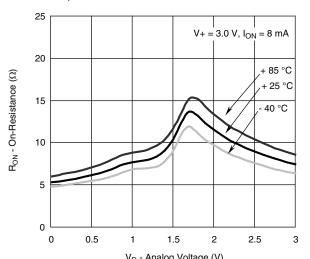
On-Resistance vs. V_D and Single Supply Voltage



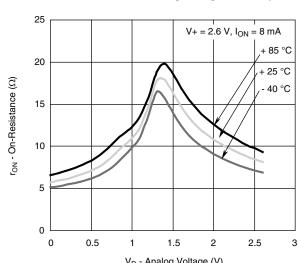
On-Resistance vs. Analog Voltage and Temperature



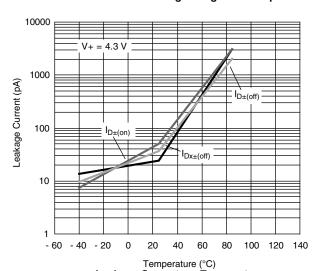
Supply Current vs. Input Switching Frequency



 $$V_{D}$$ - Analog Voltage (V) On-Resistance vs. Analog Voltage and Temperature



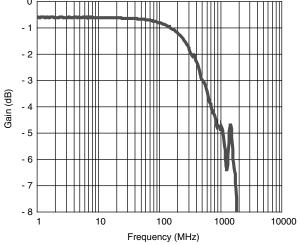
 $\label{eq:VD} {\rm V_D} \mbox{-} {\rm Analog} \mbox{ Voltage (V)} \\ {\rm \textbf{On-Resistance vs. Analog Voltage and Temperature}}$



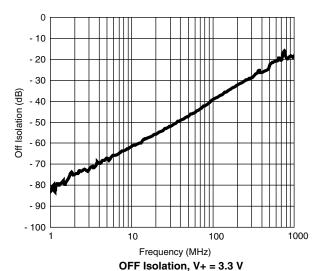
Leakage Current vs. Temperature

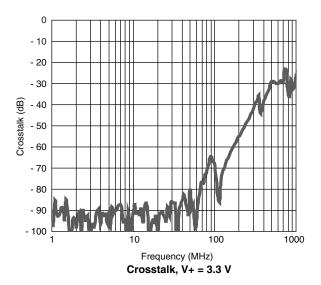
VISHAY.

TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted

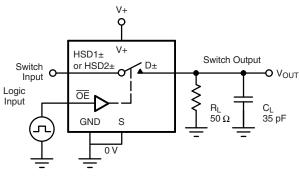


Gain vs. Frequency, C_L = 5 pF, V+ = 3.3 V



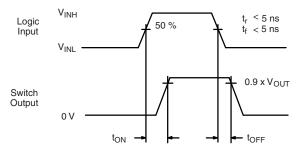


TEST CIRCUITS



 $\mathbf{C}_{\mathbf{L}}$ (includes fixture and stray capacitance)

$$V_{OUT} = D \pm \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time



TEST CIRCUITS

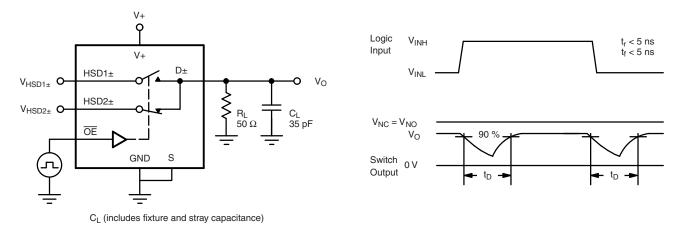


Figure 2. Break-Before-Make Interval

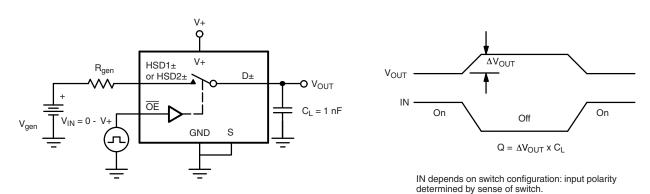


Figure 3. Charge Injection

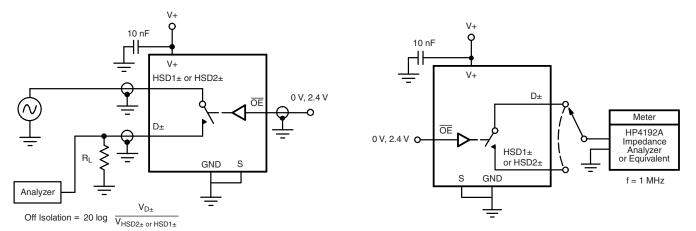
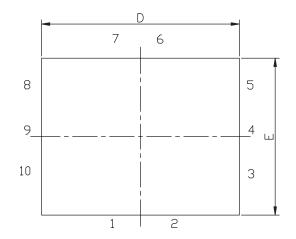


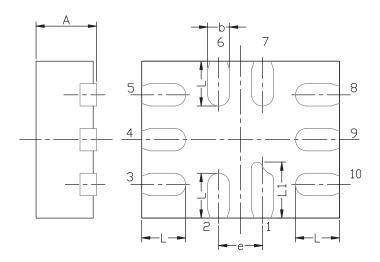
Figure 4. Off-Isolation

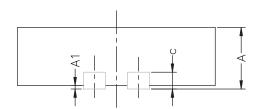
Figure 5. Channel Off/On Capacitance

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MINI QFN-10L CASE OUTLINE







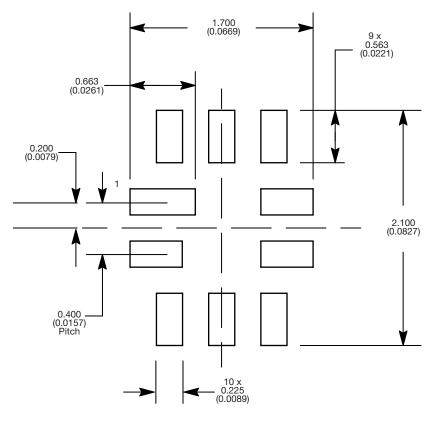
DIM	M	IILLIMETER	S	INCHES			
DIIVI	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.50	0.55	0.60	0.0197	0.0217	0.0236	
A1	0.00	-	0.05	0.000	0.002		
b	0.15	0.20	0.25	0.006 0.008 0.0			
С	0.15 REF			0.006 REF			
D	1.75	1.80	1.85	0.069 0.071 0.073			
Е	1.35	1.40	1.45	0.053	0.055	0.057	
е		0.40 BSC		0.016 BSC			
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217	

ECN T-07039-Rev. A, 12-Feb-07

DWG: 5957



RECOMMENDED MINIMUM PADS FOR MINI QFN 10L



Mounting Footprint Dimensions in mm (inch)



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Revision: 02-Oct-12 Document Number: 91000